



No.1405B

2SK436

N-Channel Junction Silicon FET

High-Frequency, Low-Frequency
General-Purpose Amp Applications

Applications

- AM tuner RF amps and low-noise amps.

Features

- Large $|Y_{fs}|$.
- Ultralow noise figure.
- Small Crss.
- Ultrasmall-sized package permitting 2SK436-applied sets to be made small and slim.

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	15	V
Gate-to-Drain Voltage	V _{GDS}	-15	V
Gate Current	I _G	10	mA
Drain Current	I _D	20	mA
Allowable Power Dissipation	P _D	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
G-D Breakdown Voltage	V _{(BR)GDS}	I _G = -10μA, V _{DS} = 0	-15			V
Gate Cutoff Current	I _{GSS}	V _{GS} = -10V, V _{DS} = 0			-1.0	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 5V, I _D = 100μA		-0.5	-1.5	V
Drain Current	I _{DSS}	V _{DS} = 5V, V _{GS} = 0	1.2*		12.0*	mA
Forward Transfer Admittance	Y _{fs}	V _{DS} = 5V, V _{GS} = 0, f = 1kHz	8.0	17		mS
Input Capacitance	C _{iss}	V _{DS} = 5V, V _{GS} = 0, f = 1MHz		7.0		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 5V, V _{GS} = 0, f = 1MHz		2.0		pF
Noise Figure	NF	V _{DS} = 5V, I _D = 1mA, R _g = 1kΩ f = 1kHz		1.5		dB

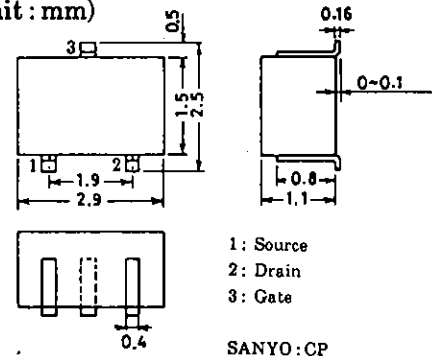
* : The 2SK436 is classified by I_{DSS} as follows : (unit : mA)

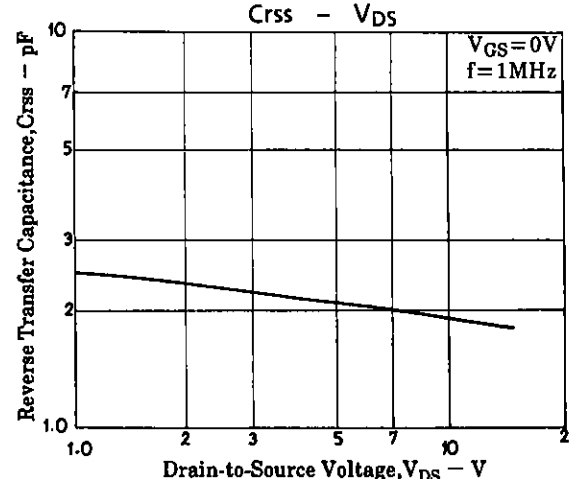
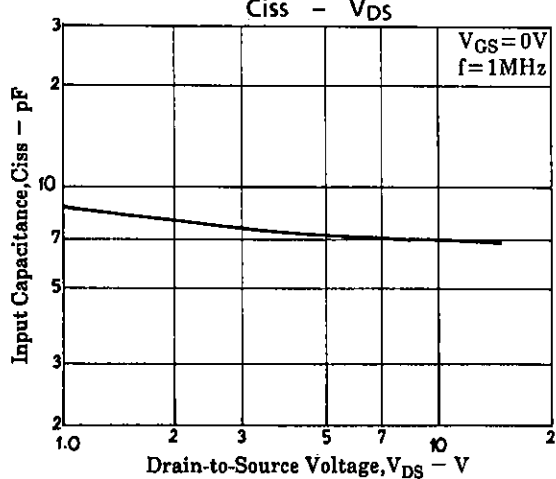
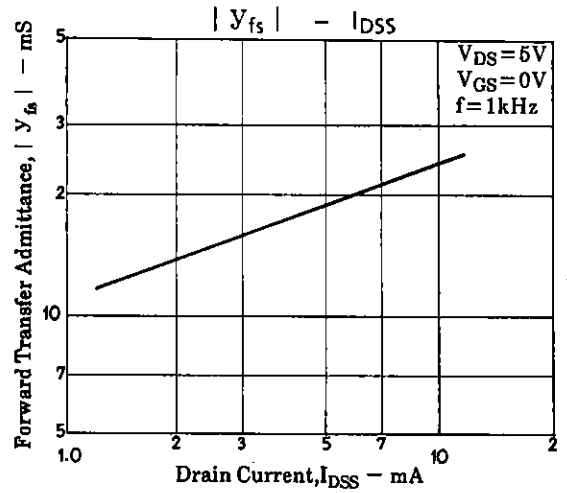
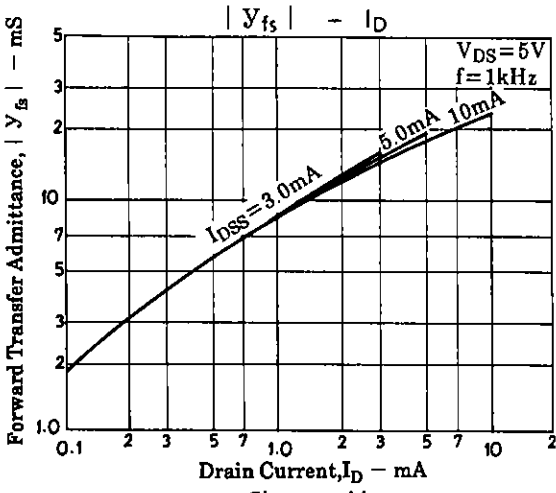
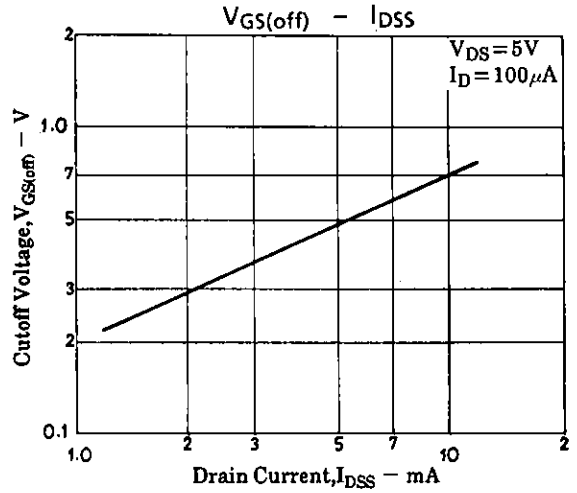
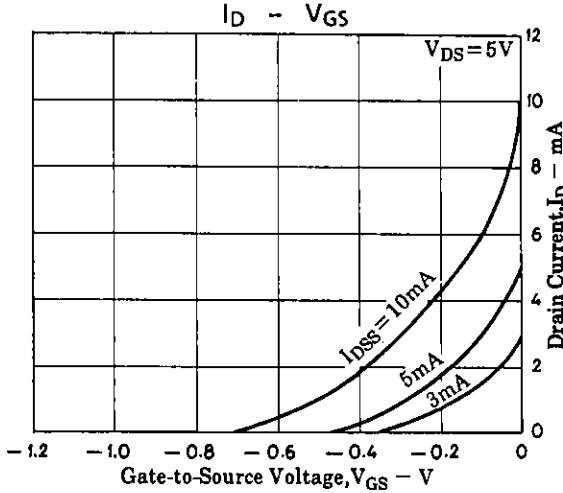
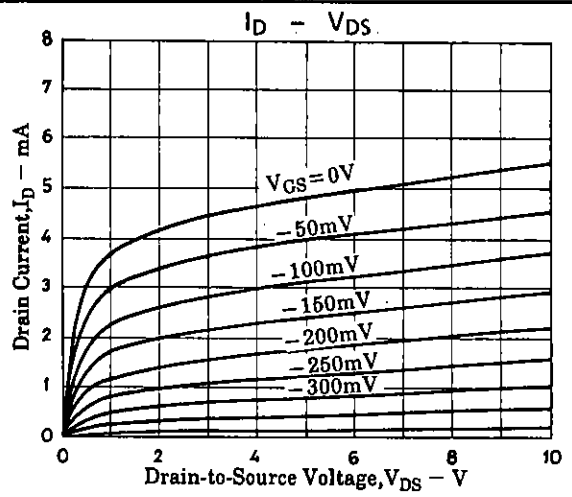
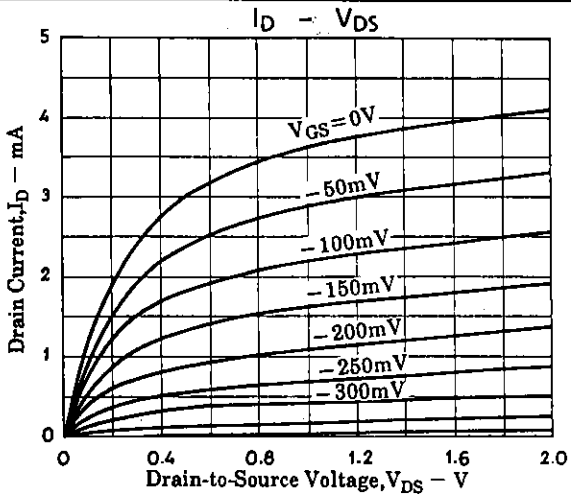
1.2	17	2.1	1.7	18	3.0	2.5	19	4.2
3.5	20	6.0	5.0	21	8.5	7.3	22	12.0

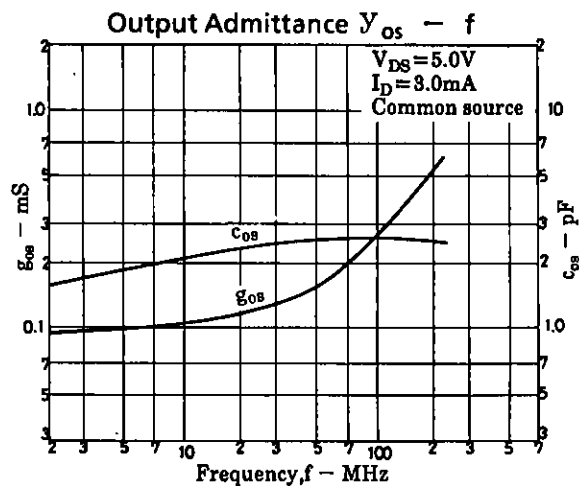
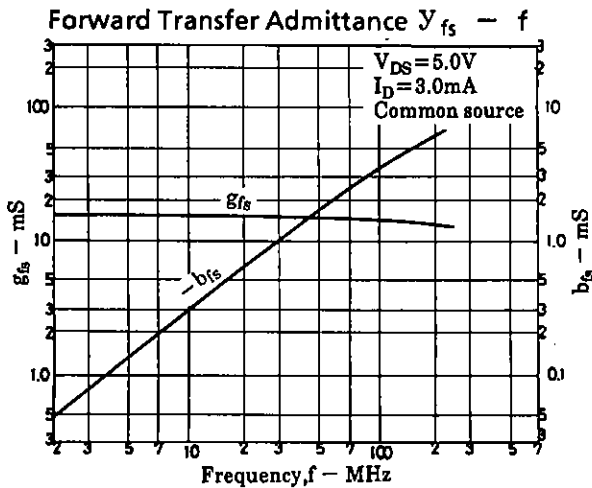
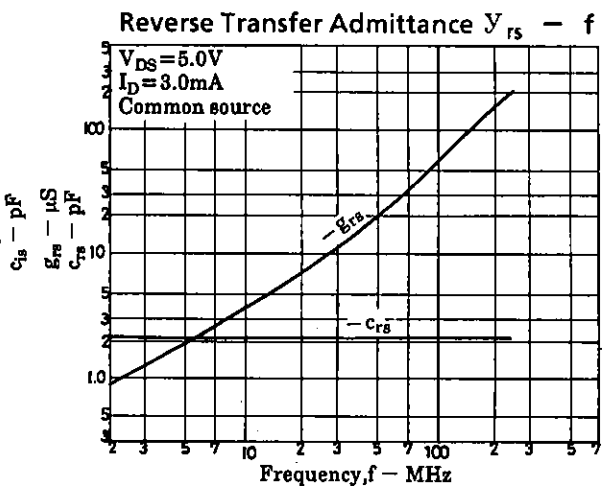
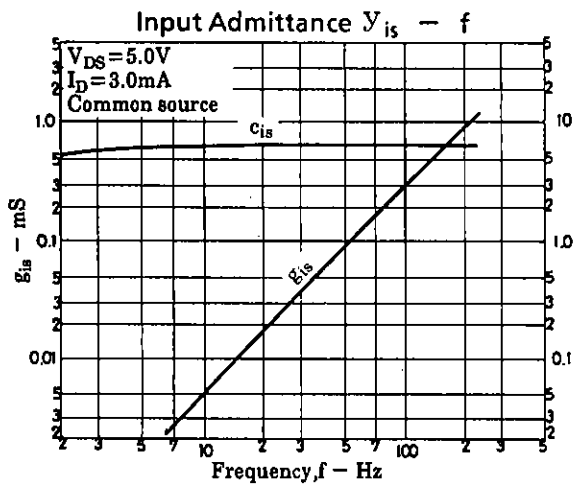
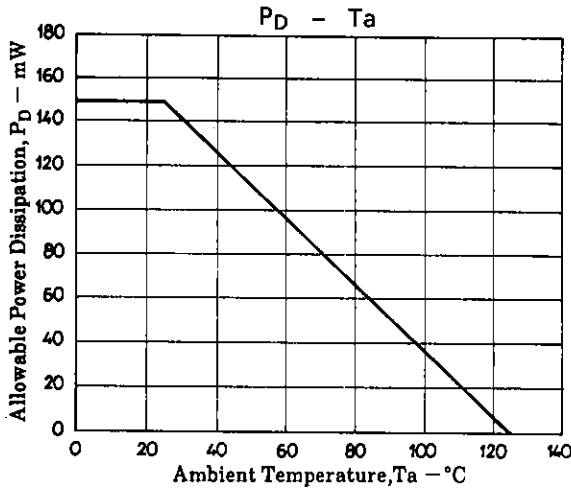
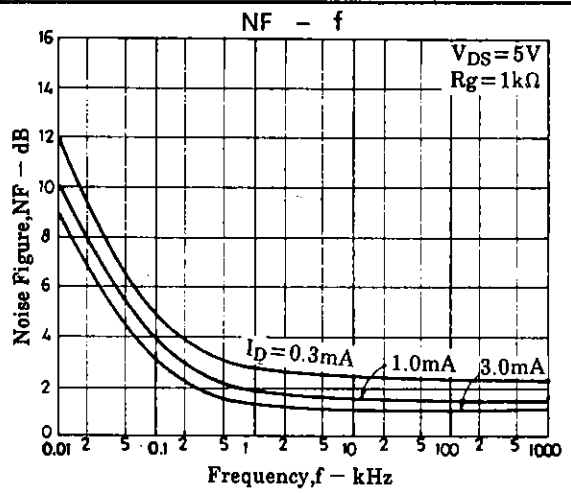
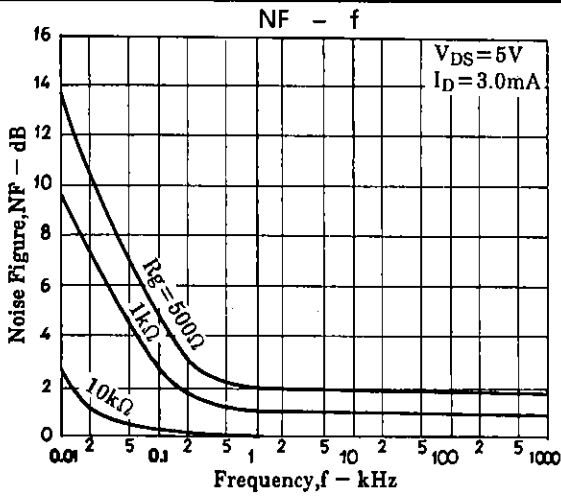
Note) Marking : A

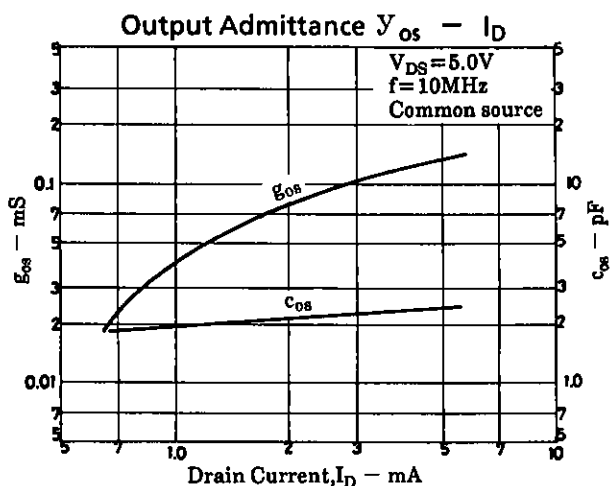
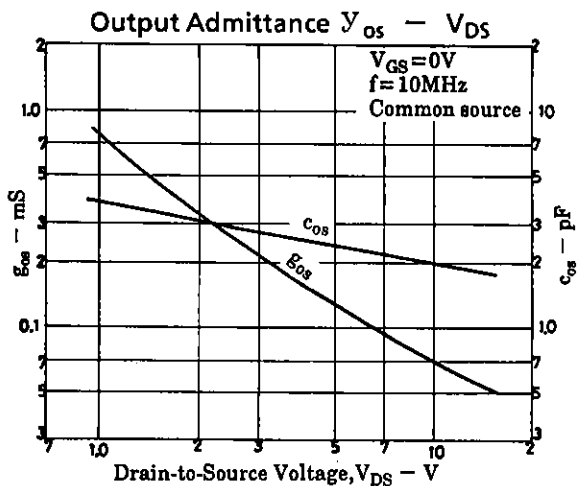
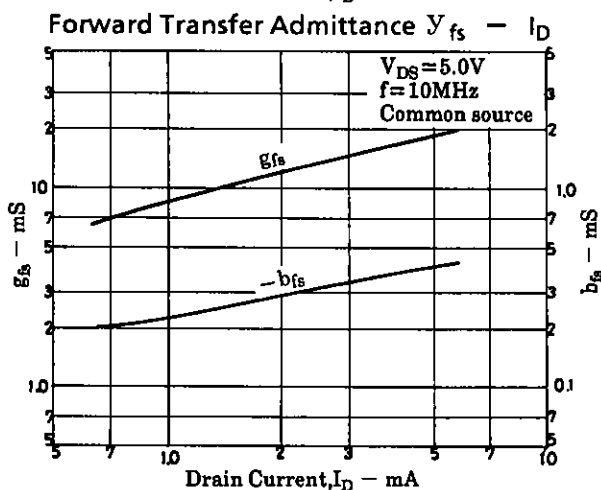
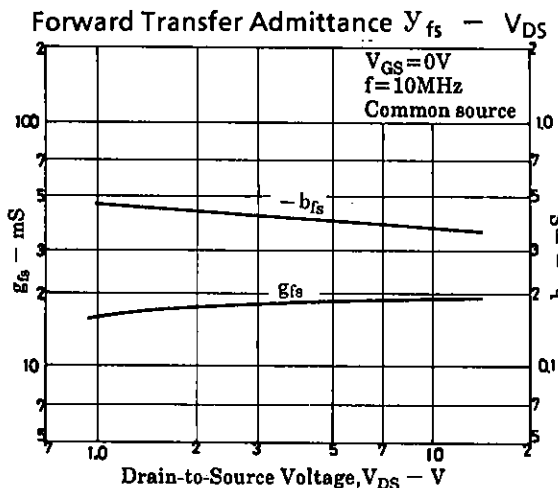
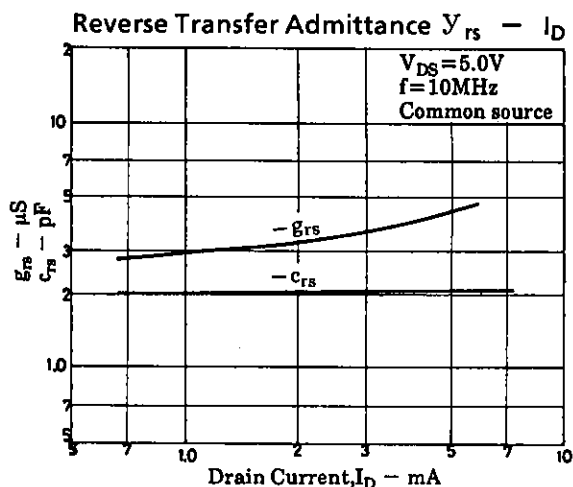
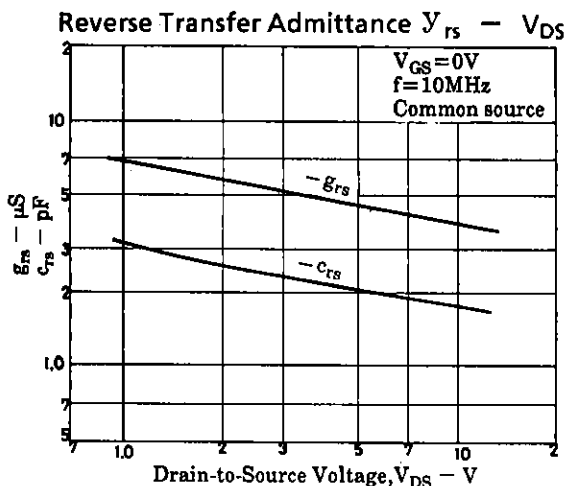
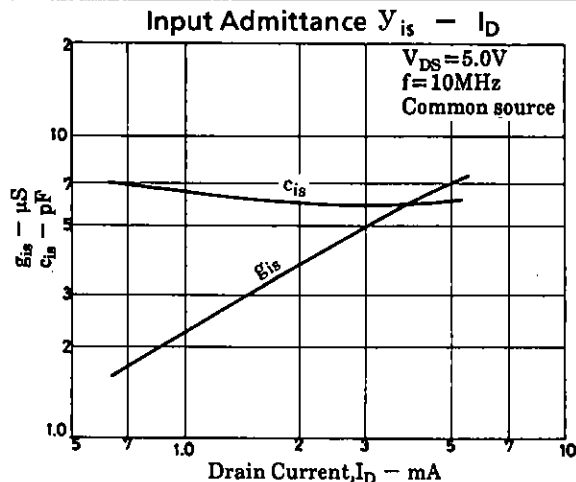
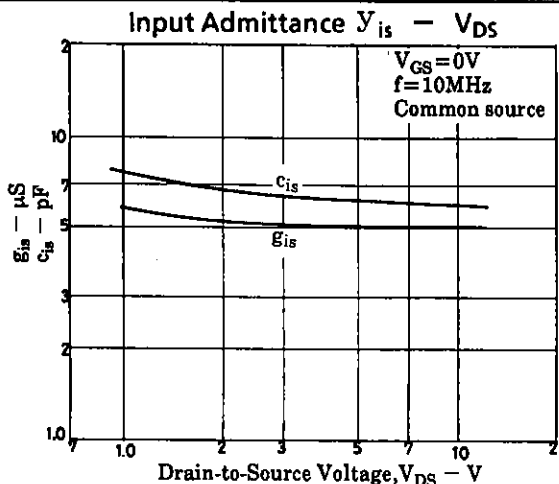
I_{DSS} rank : 17, 18, 19, 20, 21, 22

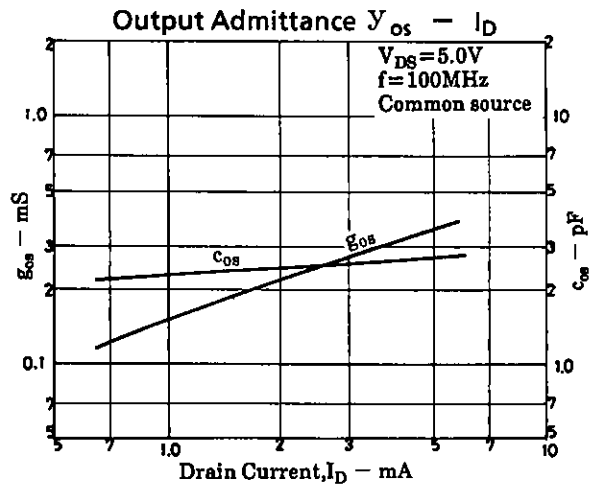
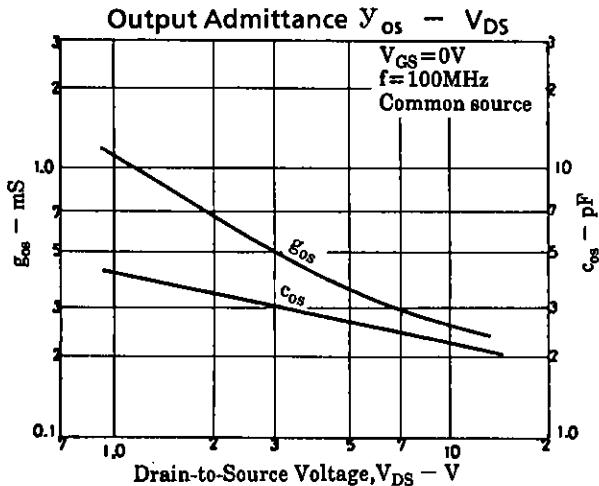
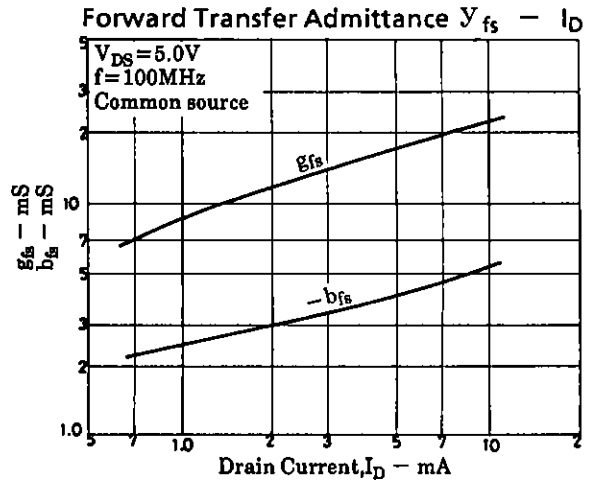
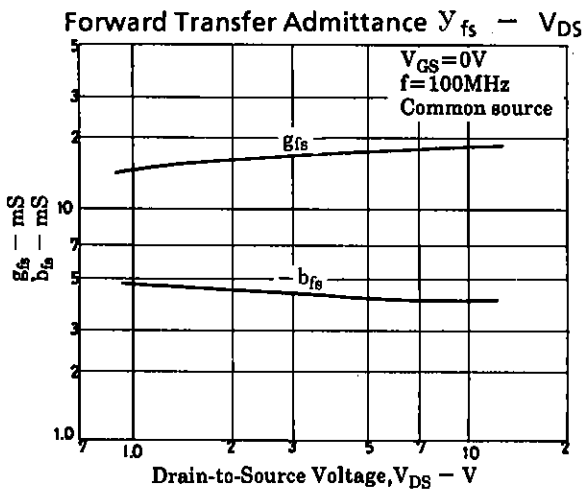
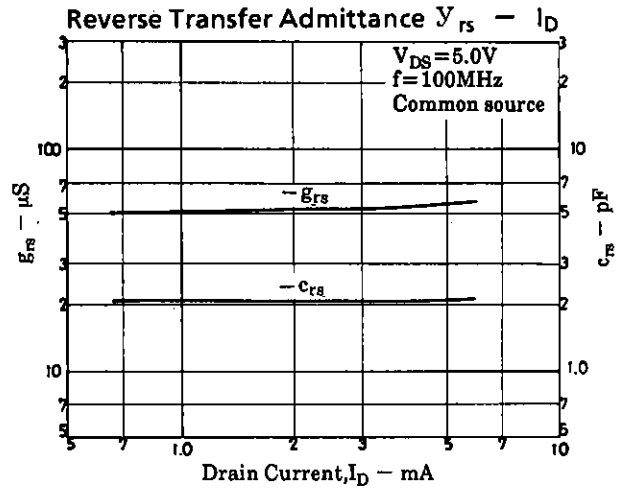
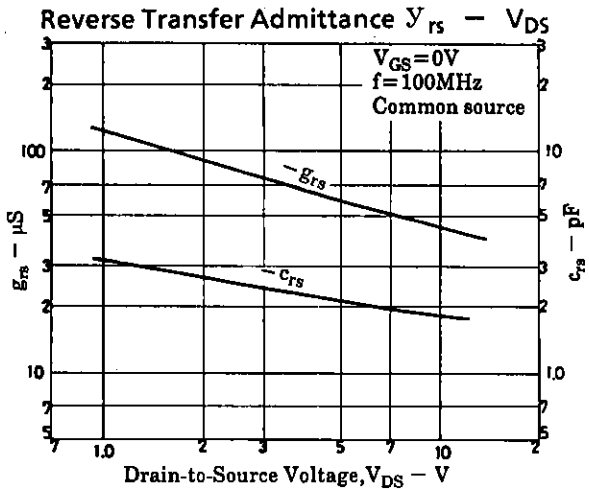
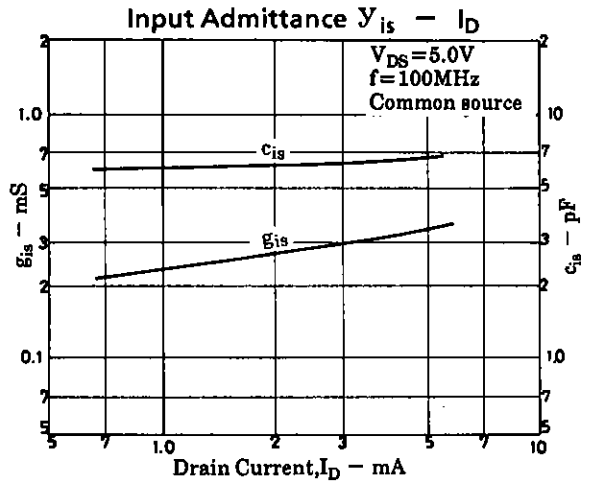
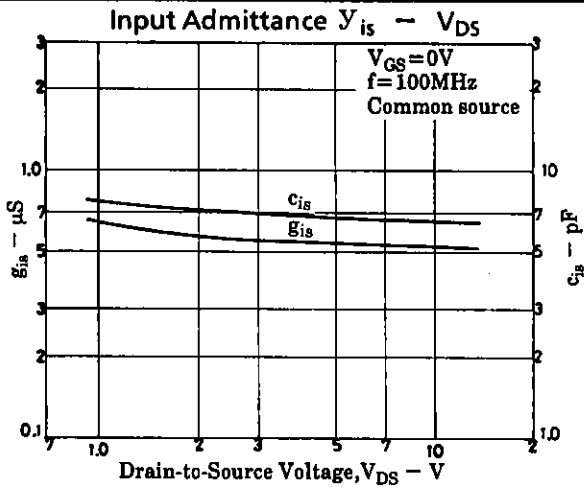
Package Dimensions 2050A
(unit : mm)

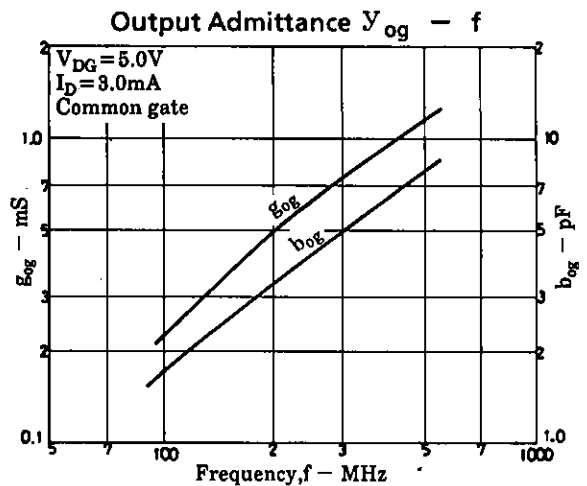
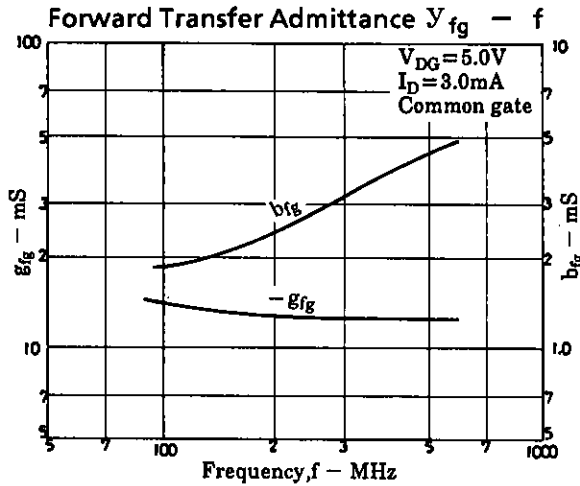
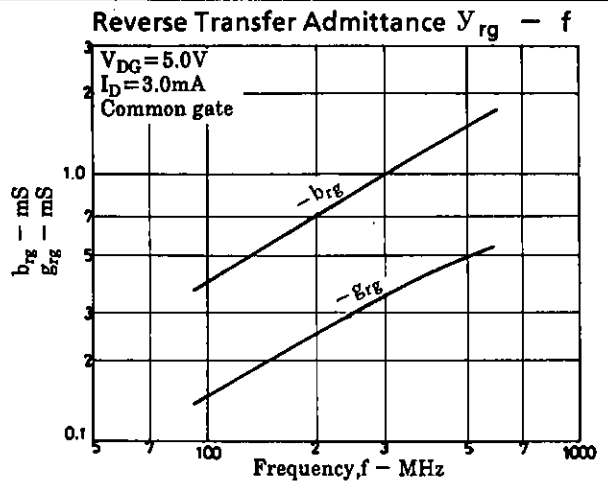
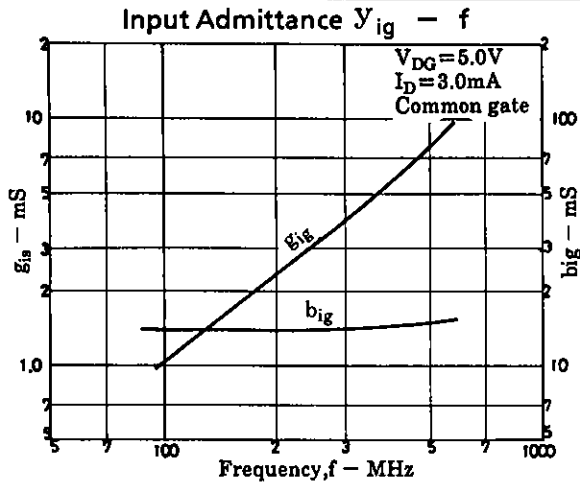












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